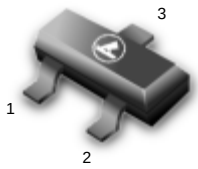
Power MOSFET
130 mAmps, 50 Volts
P–Channel SOT–323

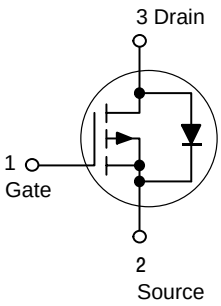
LBSS84WT1G

These miniature surface mount MOSFETs reduce power loss conserve energy, making this device ideal for use in small power management circuitry. Typical applications are dc–dc converters, load switching, power management in portable and battery–powered products such as computers, printers, cellular and cordless telephones.

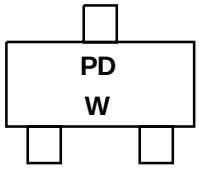
- Energy Efficient
- Miniature SOT–323 Surface Mount Package Saves Board Space
- Pb-Free Package is available.



SOT –323



Marking Diagram



W = Work Week

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 3.) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate,(Note 4.) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	°C

ORDERING INFORMATION

Device	Package	Shipping
LBSS84WT1G	SOT-323	3000/Tape&Reel
LBSS84WT1G	SOT-323	10000/Tape&Reel

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain–to–Source Voltage	V_{DSS}	50	Vdc
Gate–to–Source Voltage – Continuous	V_{GS}	± 20	Vdc
Drain Current – Continuous @ T_A = 25°C – Pulsed Drain Current ($t_p \leq 10$ µs)	 I_D I_{DM}	 130 520	mA
Total Power Dissipation @ T_A = 25°C	P_D	225	mW
Operating and Storage Temperature Range	T_J, T_{stg}	– 55 to 150	°C
Thermal Resistance – Junction–to–Ambient	$R_{\theta JA}$	556	°C/W
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	T_L	260	°C

LBSS84WT1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain–to–Source Breakdown Voltage (V_{GS} = 0 Vdc, I_D = 250 μAdc)		$V_{(BR)DSS}$	50	–	–	Vdc
Zero Gate Voltage Drain Current (V_{DS} = 25 Vdc, V_{GS} = 0 Vdc) (V_{DS} = 50 Vdc, V_{GS} = 0 Vdc) (V_{DS} = 50 Vdc, V_{GS} = 0 Vdc, T_J = 125°C)		I_{DSS}	 – – –	 – – –	 0.1 15 60	μAdc
Gate–Body Leakage Current (V_{GS} = ± 20 Vdc, V_{DS} = 0 Vdc)		I_{GSS}	–	–	±60	μAdc
ON CHARACTERISTICS (Note 1.)						
Gate–Source Threaded Voltage (V_{DS} = V_{GS}, I_D = 1.0 mAdc)		$V_{GS(th)}$	0.8	–	2.0	Vdc
Static Drain–to–Source On–Resistance (V_{GS} = 5.0 Vdc, I_D = 100 mAdc)		$r_{DS(on)}$	–	5.0	10	Ohms
Transfer Admittance (V_{DS} = 25 Vdc, I_D = 100 mAdc, f = 1.0 kHz)		$\|y_{fs}\|$	50	–	–	mS
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V_{DS} = 5.0 Vdc)	C_{iss}	–	30	–	pF
Output Capacitance	(V_{DS} = 5.0 Vdc)	C_{oss}	–	10	–	
Transfer Capacitance	(V_{DG} = 5.0 Vdc)	C_{rss}	–	5.0	–	
SWITCHING CHARACTERISTICS (Note 2.)						
Turn–On Delay Time	(V_{DD} = –15 Vdc, I_D = –2.5 Adc, R_L = 50 Ω)	$t_{d(on)}$	–	2.5	–	ns
Rise Time		t_r	–	1.0	–	
Turn–Off Delay Time		$t_{d(off)}$	–	16	–	
Fall Time		t_f	–	8.0	–	
Gate Charge		Q_T	–	6000	–	pC
SOURCE–DRAIN DIODE CHARACTERISTICS						
Continuous Current		I_S	–	–	0.130	A
Pulsed Current		I_{SM}	–	–	0.520	
Forward Voltage (Note 2.)		V_{SD}	–	2.5	–	V

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
2. Switching characteristics are independent of operating junction temperature.

TYPICAL ELECTRICAL CHARACTERISTICS

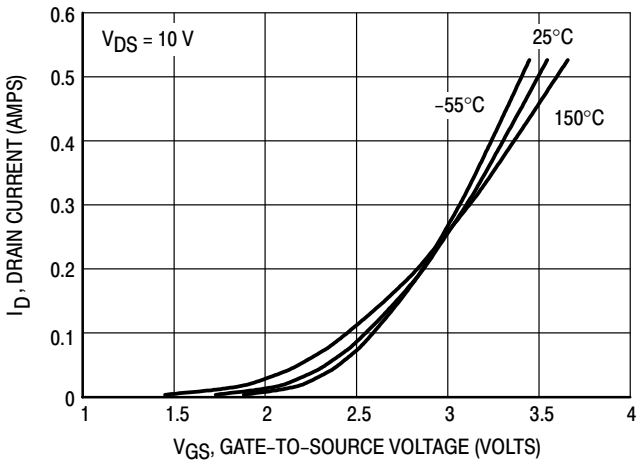


Figure 1. Transfer Characteristics

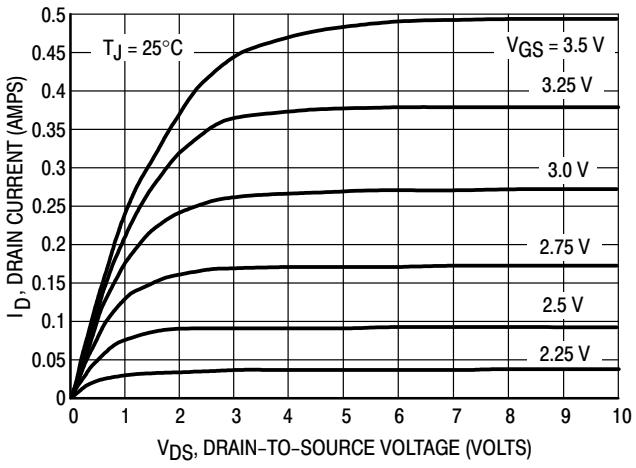


Figure 2. On–Region Characteristics

TYPICAL ELECTRICAL CHARACTERISTICS

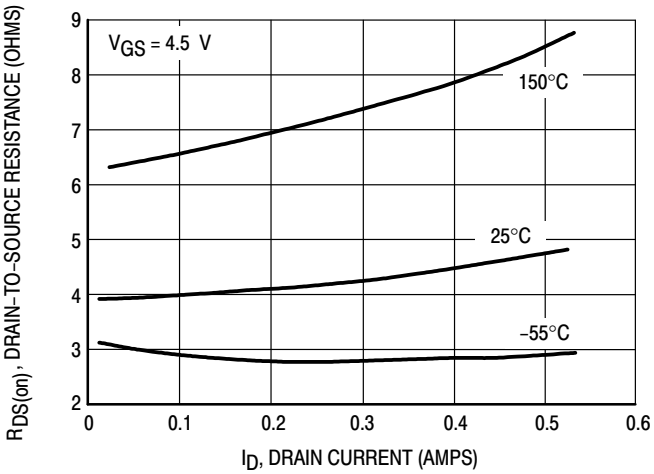


Figure 3. On–Resistance versus Drain Current

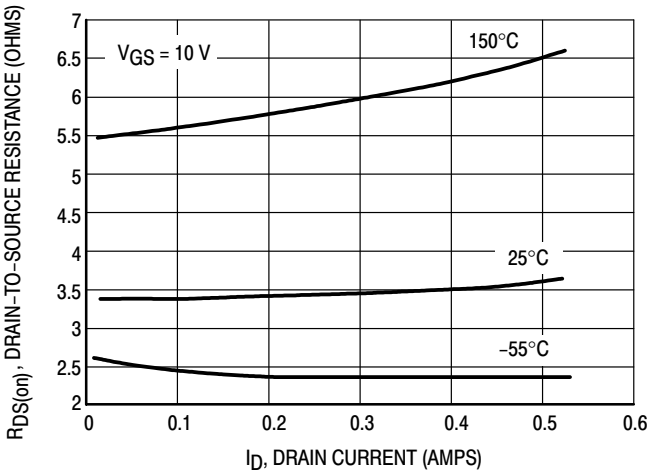


Figure 4. On–Resistance versus Drain Current

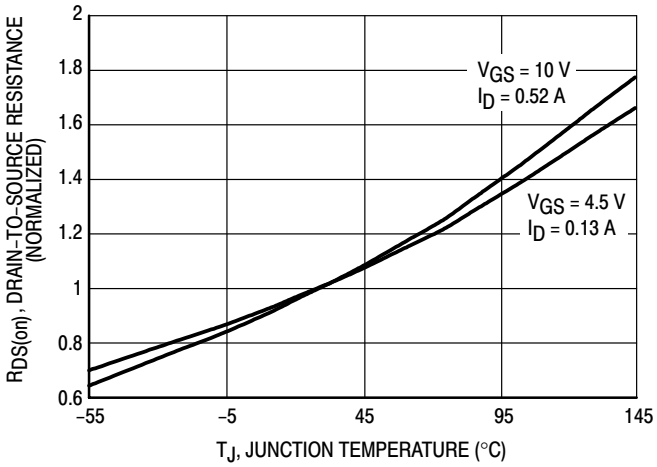


Figure 5. On–Resistance Variation with Temperature

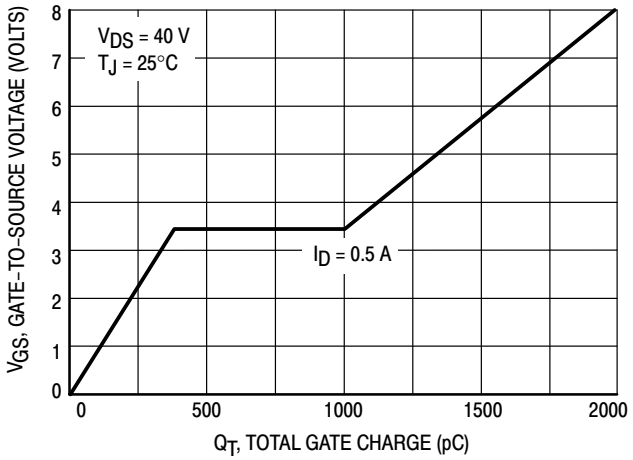


Figure 6. Gate Charge

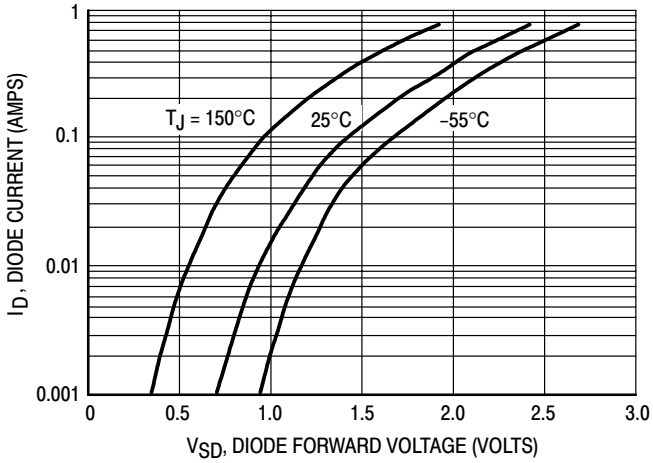
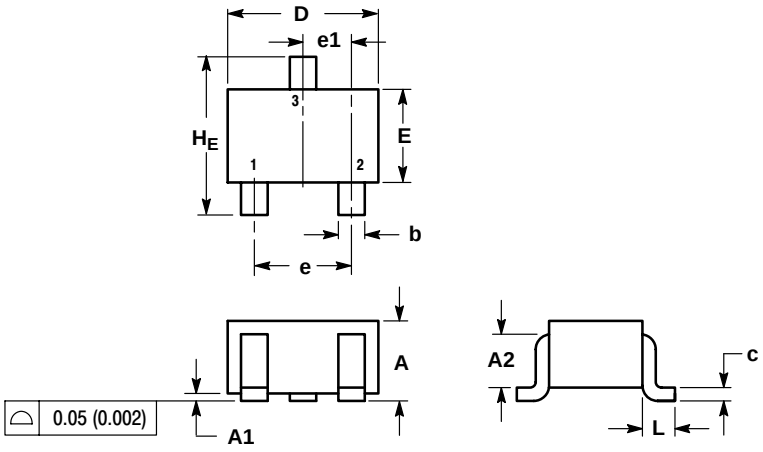


Figure 7. Body Diode Forward Voltage

LBSS84WT1G

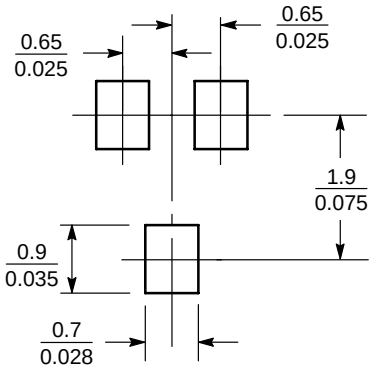
SC−70 (SOT−323)



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

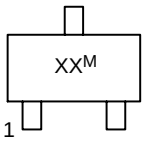
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.7 REF			0.028 REF	
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1		0.65 BSC			0.026 BSC	
L		0.425 REF			0.017 REF	
H_E	2.00	2.10	2.40	0.079	0.083	0.095

SOLDERING FOOTPRINT*



SCALE 10:1 $\left(\frac{mm}{inches}\right)$

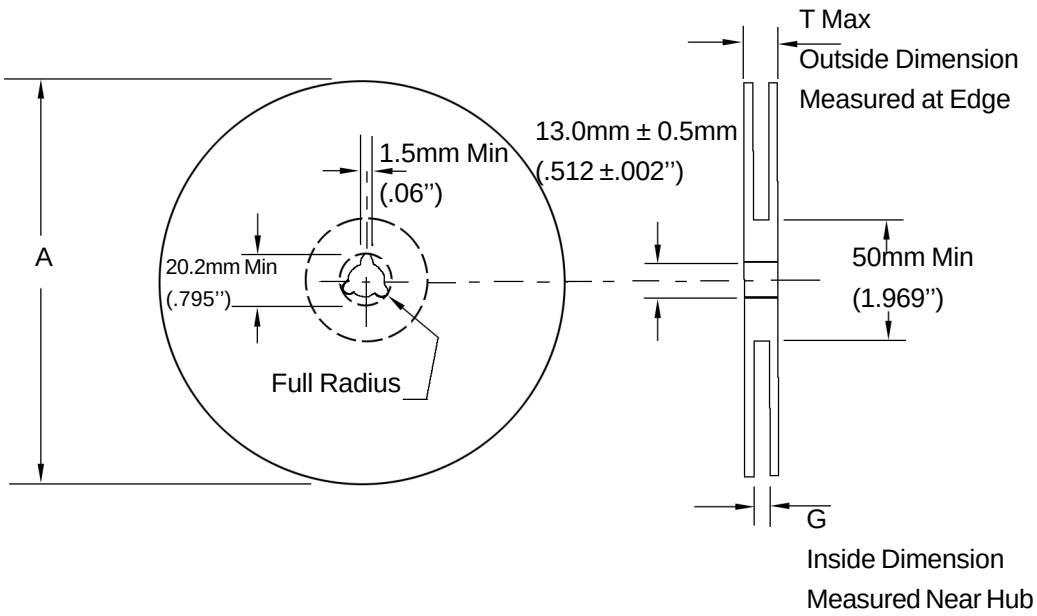
GENERIC MARKING DIAGRAM



XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

EMBOSSED TAPE AND REEL DATA
FOR DISCRETES



Size	A Max	G	T Max
8 mm	330mm (12.992")	8.4mm+1.5mm, -0.0 (.33"+.059", -0.00)	14.4mm (.56")
12mm	330mm (12.992")	12.4mm+2.0mm, -0.0 (.49 "+ .079", -0.00)	18.4mm (.72")
16mm	360mm (14.173")	16.4mm+2.0mm, -0.0 (.646"+.078", -0.00)	22.4mm (.882")
24 mm	360mm (14.173")	24.4mm+2.0mm, -0.0 (.961"+.070", -0.00)	30.4mm (1.197")

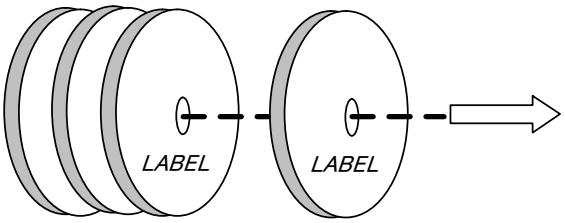
Reel Dimensions

Metric Dimensions Govern — English are in parentheses for reference only

Storage Conditions

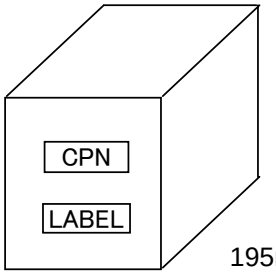
Temperature: 5 to 40 Deg.C (20 to 30 Deg. C is preferred)
Humidity: 30 to 80 RH (40 to 60 is preferred)
Recommended Period: One year after manufacturing
(This recommended period is for the soldering condition only. The characteristics and reliabilities of the products are not restricted to this limitation)

Shipment Specification



10 Reel

3000PCS/Reel
8000PCS/Reel (SOT-723,SOD-723)



Dim(Unit:mm)

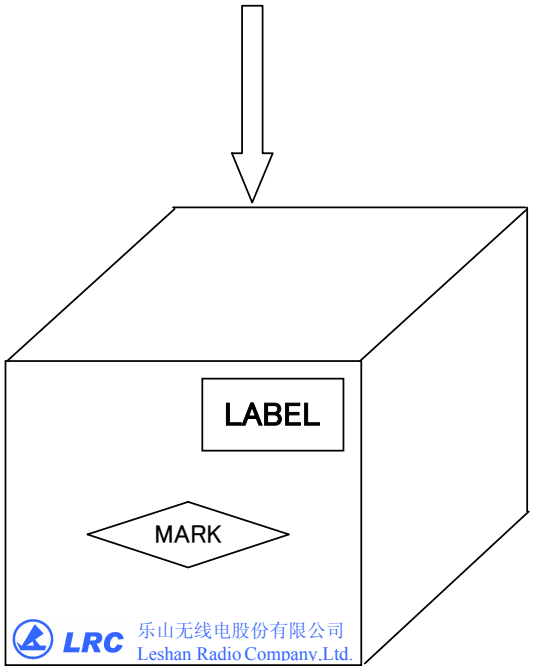
195mm*195mm*150mm

10Reel/Inner Box

30KPCS/Inner Box
80KPCS/Inner Box (SOT-723,SOD-723)

Dim(Unit:mm)

460mm*400mm*420mm



12 Inner Box/Carton

360KPCS/Carton
960KPCS/Carton (SOT-723,SOD-723)